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5/23/02

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): T. ONO, et al

Serial No.: 09/249,292

Filed: February 12, 1999

For: METHOD AND APPARATUS FOR TREATING SURFACE OF SEMICONDUCTOR

Group: 1746

Examiner: A. Olsen

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AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

May 20, 2002

Sir:

The following amendments and remarks are respectfully submitted in connection with the above-identified application in response to the Office Action dated December 18, 2001.

IN THE CLAIMS:

Please amend claims 1 and 2 as follows:

1. (amended) A method of treating a surface of a sample, comprising the steps of:
generating a plasma in a treatment chamber;
applying an rf bias voltage of a frequency sufficient to form an ion energy distribution including a high peak point at which the ion energy has high directionality and a low peak

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